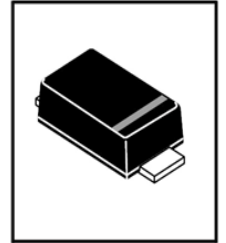


特性/机械性能:
FEATURES/MECHANICAL DATE

- ◆ 总功耗:最大500mW
The total power consumption: maximum 500mW
- ◆ 封装: SOD-123模塑封装
Case: SOD – 123, molded plastic
- ◆ 电压范围: 2.0 to 120V
Voltage range 2.0 to 120V
- ◆ 参数误差在 ±5%
±5% voltage tolerance
- ◆ 硅齐纳 (稳压) 二极管 Silicon zener diode



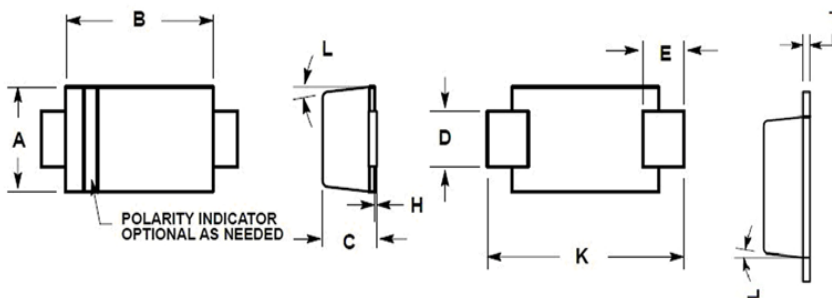
SOD-123

最大额定值及电气特性:
MAXIMUM RATINGS AND CHARACTERISTICS

测量环境温度25℃, 除非另有规定.

Rating at 25℃ ambient temperature unless otherwise specified.

参数名称 PAPT NUMBER	符号Symbol	数值Value	单位Unit
耗散功率 Power Dissipation	Pt	500	mW
正向电压@IF = 10 mA . Forward voltage@IF=10mA	V _F	0.9	V
热阻抗 (结至周围环境) Thermal impedance (junction to ambient)	R _{θ(ja)}	340	℃/W
使用及储存温度范围 Operating and Storage Temperature Range	T _J , T _{STG}	-55~+150	℃

产品外形尺寸:
PRODUCT APPEARANCE SIZE


DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.50	1.80	0.059	0.071
B	2.50	2.90	0.098	0.114
C	0.90	1.20	0.035	0.047
D	0.70	1.10	0.028	0.043
E	0.50	0.95	0.020	0.037
H	0.00	0.10	0.000	0.004
J	0.10	0.20	0.004	0.008
K	3.40	3.90	0.134	0.154
L	0°	8°	0°	8°

电特性:
ELECTRICAL CHARACTERISTICS

型号 TYPE	代码 Marking	齐纳电压 Zener voltage			最大齐纳阻抗 Maximum dynamic resistance		最大反向漏电流 Maximum Leakage Current @VR		温度系数 Temperature coefficient
		Vznom V	IZT for VZT		Zz (Max) at IZ		IR(Max)at VR		TKVZ %/K
			mA	V	Ω	mA	μA	V	
MM1Z2V0	4A	2.0	5	1.80...2.15	100	5	120	0.5	-0.09...-0.06
MM1Z2V2	4B	2.2	5	2.08...2.33	100	5	120	0.7	-0.09...-0.06
MM1Z2V4	4C	2.4	5	2.28...2.56	100	5	120	1.0	-0.09...-0.06
MM1Z2V7	4D	2.7	5	2.5...2.9	110	5	120	1.0	-0.09...-0.06
MM1Z3V0	4E	3.0	5	2.8...3.2	120	5	50	1.0	-0.08...-0.05
MM1Z3V3	4F	3.3	5	3.1...3.5	130	5	20	1.0	-0.08...-0.05
MM1Z3V6	4H	3.6	5	3.4...3.8	130	5	10	1.0	-0.08...-0.05
MM1Z3V9	4J	3.9	5	3.7...4.1	130	5	10	1.0	-0.08...-0.05
MM1Z4V3	4K	4.3	5	4.0...4.6	130	5	10	1.0	-0.06...-0.03
MM1Z4V7	4M	4.7	5	4.4...5.0	130	5	10	1.0	-0.05...+0.02
MM1Z5V1	4N	5.1	5	4.8...5.4	130	5	5	1.5	-0.02...+0.02
MM1Z5V6	4P	5.6	5	5.2...6.0	80	5	5	2.5	-0.05...+0.05
MM1Z6V2	4R	6.2	5	5.8...6.6	50	5	2	3.0	0.03...0.06
MM1Z6V8	4X	6.8	5	6.4...7.2	30	5	2	3.5	0.03...0.07
MM1Z7V5	4Y	7.5	5	7.0...7.9	30	5	2	4.0	0.03...0.07
MM1Z8V2	4Z	8.2	5	7.7...8.7	30	5	2	5.0	0.03...0.08
MM1Z9V1	5A	9.1	5	8.5...9.6	30	5	2	6.0	0.03...0.09
MM1Z10	5B	10	5	9.4...10.6	30	5	2	7.0	0.03...0.1
MM1Z11	5C	11	5	10.4...11.6	30	5	2	8.0	0.03...0.11
MM1Z12	5D	12	5	11.4...12.7	35	5	2	9.0	0.03...0.11
MM1Z13	5E	13	5	12.4...14.1	35	5	2	10	0.03...0.11
MM1Z15	5F	15	5	13.8...15.6	40	5	2	11	0.03...0.11
MM1Z16	5H	16	5	15.3...17.1	40	5	2	12	0.03...0.11
MM1Z18	5J	18	5	16.8...19.1	45	5	2	13	0.03...0.11
MM1Z20	5K	20	5	18.8...21.2	50	5	2	15	0.03...0.11
MM1Z22	5M	22	5	20.8...23.3	55	5	2	17	0.04...0.12
MM1Z24	5N	24	5	22.8...25.6	60	5	2	19	0.04...0.12
MM1Z27	5P	27	5	25.1...28.9	70	2	2	21	0.04...0.12
MM1Z30	5R	30	5	28...32	80	2	2	23	0.04...0.12
MM1Z33	5X	33	5	31...35	80	2	2	25	0.04...0.12
MM1Z36	5Y	36	5	34...38	90	2	2	27	0.04...0.12
MM1Z39	5Z	39	2.5	37...41	100	2	2	30	0.04...0.12
MM1Z43	6A	43	2.5	40...46	130	2	2	33	0.04...0.12
MM1Z47	6B	47	2.5	44...50	150	2	2	36	0.04...0.12
MM1Z51	6C	51	2.5	48...54	180	2	1	39	0.04...0.12
MM1Z56	6D	56	2.5	52...60	180	2	1	43	0.04...0.12
MM1Z62	6E	62	2.5	58...66	200	2	0.2	47	0.04...0.12
MM1Z68	6F	68	2.5	64...72	250	2	0.2	52	0.04...0.12
MM1Z75	6H	75	2.5	70...79	300	2	0.2	57	0.04...0.12

电特性:
ELECTRICAL CHARACTERISTICS

型号 TYPE	代码 Marking	齐纳电压 Zener voltage			最大齐纳阻抗 Maximum dynamic resistance		最大反向漏电流 Maximum Leakage Current @VR		温度系数 Temperature coefficient
		Vznom V	IZT for VZT		Zz (Max) at IZ		IR(Max)at VR		TKVZ %/K
			mA	V	Ω	mA	μA	V	
MM1Z82	6J	82	2.5	77...87	300	2	0.2	63	0.05...0.12
MM1Z91	6K	91	1	85...96	700	1	0.2	69	0.05...0.12
MM1Z100	6M	100	1	94...106	700	1	0.2	76	0.05...0.12
MM1Z110	6N	110	1	104...116	800	1	0.2	84	0.05...0.12
MM1Z120	6P	120	1	114...127	900	1	0.2	91	0.05...0.12

- 1) VZ is tested with pulses (20 ms).
 - 2) ZZ is measured at I by given a very small A.C. current signal.
- Breakdown characteristics T_J=constant (pulse)

特性曲线图:
RATINGS AND CHARACTERISTIC CURVES
